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Abstract

The invention relates to a semiconductor device, having

- a substrate (8), the process surface (8') of which has a substrate-normal direction;
- at least a first contact (12, 16, 22, 24, 26) and a second contact (14) arranged on the substrate, a contact surface of the second contact (14) being at a greater distance, in the substrate-normal direction, from the substrate (8) than a contact surface of the first contact (12, 16, 22, 24, 26); and
- at least a first (34) and a second (40) patterned metal plane, in each of which at least one conductor, which can be connected to at least one of the contacts, is formed;

the second metal plane (40) being at a greater distance, in the substrate-normal direction, from the substrate (8) than the first metal plane (34),
the second contact (14) being electrically connected to a conductor, located above it in the substrate-normal direction, of the second metal plane (40) without a conductor of the first metal plane (34) being electrically connected in between, and
the first contact (12, 16, 22, 24, 26) being electrically connected to a conductor, located above it in the substrate-normal direction, of the first metal plane (34).

(Fig. 14)

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